

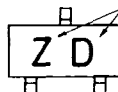
Unit in mm

[illegible]

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-30	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-4	V
Collector Current	I_C	-200	mA
Base Current	I_B	-50	mA
Collector Power Dissipation ($T_a=25^\circ\text{C}$) Derate Linearly 25°C	P_C	200	mW
		1.6	mW/ $^\circ\text{C}$
Thermal Resistance (Junction to Ambient)	$R_{th(j-a)}$	625	$^\circ\text{C/W}$
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 ~ 150	$^\circ\text{C}$

Type Name



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	ICBO	V _{CB} =-20V, I _E =0	-	-	-50	nA
Emitter Cut-off Current	IEBO	V _{EB} =-3V, I _C =0	-	-	-50	nA
Collector-Base Breakdown Voltage	V _(BR) CBO	I _C =-10μA, I _E =0	-30	-	-	V
Collector-Emitter Breakdown Voltage	V _(BR) CEO	I _C =-1mA, I _B =0	-30	-	-	V
Emitter-Base Breakdown Voltage	V _(BR) EBO	I _E =-10μA, I _C =0	-4	-	-	V
DC Current Gain	h _{FE} (1)	V _{CE} =-1V, I _C =-2mA	50	-	150	
	h _{FE} (2)	V _{CE} =-1V, I _C =-50mA	25	-	-	
Collector-Emitter Saturation Voltage	V _{CE} (sat)	I _C =-50mA, I _B =-5mA	-	-	-0.4	V
Base-Emitter Saturation Voltage	V _{BE} (sat)	I _C =-50mA, I _B =-5mA	-	-	-0.95	V
Small Signal Forward Current Transfer Ratio	h _{fe}	V _{CE} =-20V, I _C =-10mA f=100MHz	2.0	-	-	
Transition Frequency	f _T	V _{CE} =-20V, I _C =-10mA f=100MHz	200	-	-	MHz
Collector Output Capacitance	C _{ob}	V _{CB} =-5V, I _E =0, f=1MHz	-	-	4.5	pF
Input Capacitance	C _{ib}	V _{EB} =-0.5V, I _C =0, f=1MHz	-	-	10	pF
Small Signal Current Gain	h _{fe}	V _{CE} =-10V, I _C =-2mA, f=1kHz	50	-	200	
Noise Figure	NF	V _{CE} =-5V, I _C =-100μA R _g =1kΩ, f=10Hz ~ 15.7kHz	-	-	5	dB